

TRANSISTOR MODULE

QCA75AA120



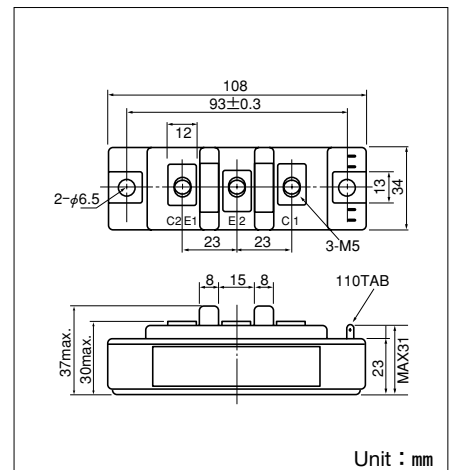
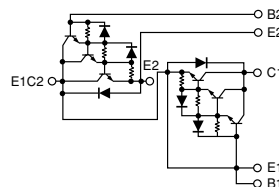
UL;E76102 (M)

QCA75AA120 is a dual Darlington power transistor module which has series-connected high speed, high power Darlington transistors. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction,

- $I_C=75A$, $V_{CEX}=1200V$
- Low saturation voltage for higher efficiency.
- High DC current gain h_{FE}
- Isolated mounting base

(Applications)

Motor Control (VVF), AC/DC Servo, UPS,
Switching Power Supply, Ultrasonic Application



Maximum Ratings

($T_j=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Item | | Conditions | Ratings | | Unit |
|-----------|---------------------------|---------------|-----------------------------------|-------------|--|------------------|
| | | | | QCA75AA120 | | |
| V_{CBO} | Collector-Base Voltage | | | 1200 | | V |
| V_{CEX} | Collector-Emitter Voltage | | $V_{BE}=-2V$ | 1200 | | V |
| V_{EBO} | Emitter-Base Voltage | | | 10 | | V |
| I_C | Collector Current | | | 75 | | A |
| $-I_C$ | Reverse Collector Current | | | 75 | | A |
| I_B | Base Current | | | 4 | | A |
| P_T | Total power dissipation | | $T_C=25^\circ\text{C}$ | 500 | | W |
| T_j | Junction Temperature | | | -40 to +150 | | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | | | -40 to +125 | | $^\circ\text{C}$ |
| V_{ISO} | Isolation Voltage | | A.C.1minute | 2500 | | V |
| | Mounting Torque | Mounting (M6) | Recommended Value 2.5-3.9 (25-40) | 4.7 (48) | | N·m (kgf·cm) |
| | | Terminal (M5) | Recommended Value 1.5-2.5 (15-25) | 2.7 (28) | | |
| | Mass | | Typical Value | 250 | | g |

Electrical Characteristics

| Symbol | Item | | Conditions | Ratings | | Unit |
|----------------|--------------------------------------|--------------|---|---------|------|---------------------------|
| | | | | Min. | Max. | |
| I_{CBO} | Collector Cut-off Current | | $V_{CB}=1200V$ | | 1.0 | mA |
| I_{EBO} | Emitter Cut-off Current | | $V_{EB}=10V$ | | 300 | mA |
| $V_{CEX(SUS)}$ | Collector Emitter Sustaining Voltage | | $I_C=15A$, $I_{B2}=-3A$ | 1200 | | V |
| h_{FE} | DC Current Gain | | $I_C=75A$, $V_{CE}=5V$ | 75 | | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | | $I_C=75A$, $I_B=1.5A$ | | 3.0 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | | $I_C=75A$, $I_B=1.5A$ | | 3.5 | V |
| t_{on} | Switching Time | On Time | $V_{CC}=600V$, $I_C=75A$ $I_{B1}=1.5A$, $I_{B2}=-1.5A$ | | 2.5 | μs |
| t_s | | Storage Time | | | 15.0 | |
| t_f | | Fall Time | | | 3.0 | |
| V_{ECO} | Collector-Emitter Reverse Voltage | | $-I_C=75A$ | | 1.8 | V |
| $R_{th(j-c)}$ | Thermal Impedance (junction to case) | | Transistor part | | 0.25 | $^\circ\text{C}/\text{W}$ |
| | | | Diode part | | 1.2 | |

